

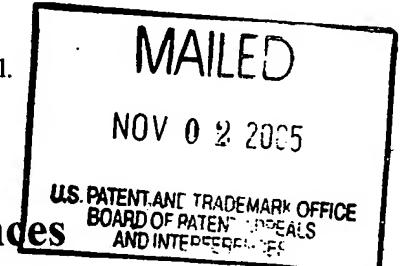


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BIRCH STEWART KOLASCH & BIRCH
PO BOX 747
FALLS CHURCH, VA 22040-0747

Paper No:
Appeal No: 2006-0108
Application: 09/980,620
Appellant: Makoto Ozeki et al.



Board of Patent Appeals and Interferences Docketing Notice

Application 09/980,620 was received from the Technology Center at the Board on September 29, 2005 and has been assigned Appeal No: 2006-0108.

A review of the file indicates that the following documents have been filed by appellant:

Appeal Brief filed on: February 20, 2004
Reply Brief filed on: August 03, 2004
Request for Hearing filed on: August 03, 2004

In all future communications regarding this appeal, please include both the application number and the appeal number.

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By order of the Board of Patent Appeals and Interferences

S3	39	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with (2\$nm angstrom))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 17:47
S4	1	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with (2\$nm angstrom)) and (sidewall with silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 17:48
S5	39	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with (2\$nm angstrom))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 17:50
S6	39	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with (2\$nm angstrom ".ANG."))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 08:10